

SiBP7R4/3-9D2

Features

- High precision
- MEMS process
- High performance, shielded, Micro-Cavity structure
- Silicon base, 50 Ω CPW output
- Au bonding for MCM application

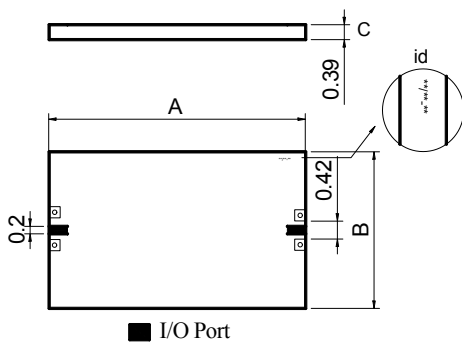
Environmental Parameter

Operating Temperature	-55°C~+85°C
Storage Temperature	-55°C~+125°C
Highest Input Power	35dBm

Electrical Parameter(TA=+25°C)

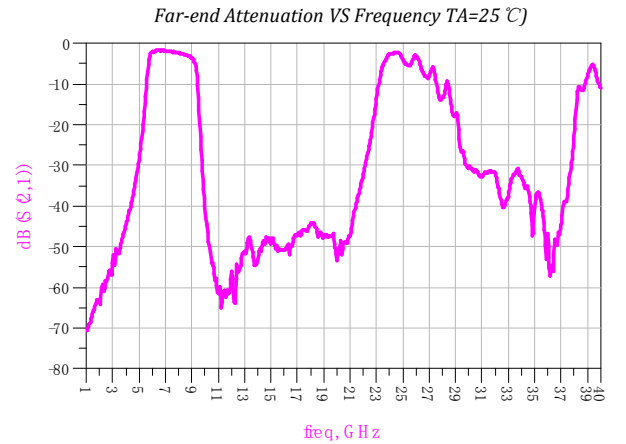
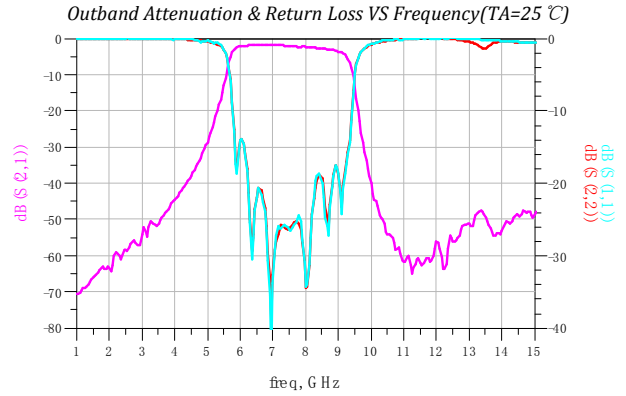
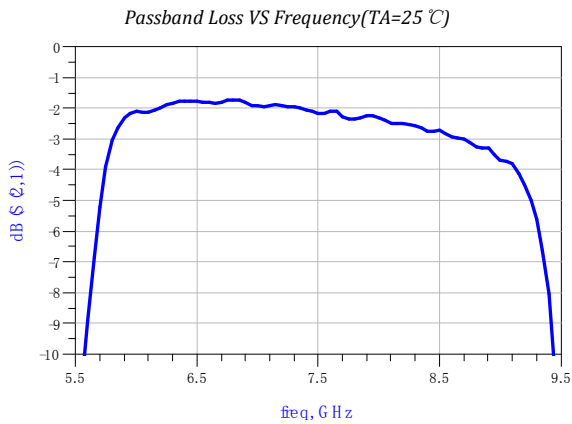
Item	Min.	Typical	Max.	Unit
Central Frequency(f_0)	-	7.4	-	GHz
Passband Frequency Range	5.9	-	8.9	GHz
Passband Ripple	-	-	1	dB
Central Insertion Loss	-	3	-	dB
Return Loss	-	15	-	dB
Out Band Attenuation	≥ 35 @4.7GHz			dB
	≥ 35 @10.1GHz			dB

Overall Dimension

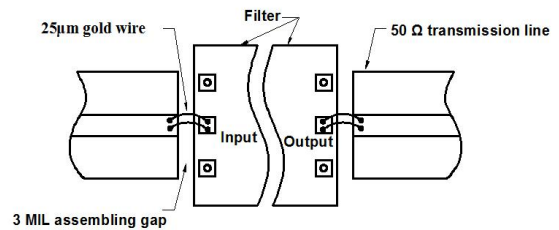


Dimension Symbols	Value(mm)		
	Min.	Nominal	Max.
A	7.9	-	8
B	4.1	-	4.2

Typical Testing Curve



Assembly Diagram



Note:

1. Au bonding ribbon width=150um, thickness=12.5um, as short as possible.
2. Recommended space between chip and cover:1-3mm
3. Low temperature assembly technology:180°C Max
4. The center RF stripline of CPW can be connected directly to the microstrip line of customer.
5. Top surface bonded to Ground is helpful for high I stopband rejection.
6. Underlayered metal: Cova (recommended).

